Supporting Information

“Resistive Switching Characteristics of Li-doped ZnO Thin Films based on Magnetron Sputtering”

1. Multiple $I$-$V$ characteristics of the resulted devices under a DC voltage.

![Figure S1. The $I$-$V$ characteristics: (a) device-A; (b) device-B; (c) device-C; (d) device-D.](image)

2. The curves of cumulative distributions and the coefficient of variation ($\sigma/\mu$) of $R_{LRS}$ and $R_{HRS}$

![Figure S2. (a) The cumulative distributions of $R_{LRS}$ and $R_{HRS}$; (b) The coefficient of](image)
variation of $R_{LRS}$ and $R_{HRS}$ distribution.

3. The endurance characteristics of resistive switching device.

**Figure S3.** The endurance performances of (a) device-A; (b) device-B; (c) device-D.